Very Low Forward Voltage Trench-based Schottky Rectifier

Exceptionally Low $V_F = 0.42 \text{ V}$ at $I_F = 5 \text{ A}$

Features

- Fine Lithography Trench-based Schottky Technology for Very Low Forward Voltage and Low Leakage
- Fast Switching with Exceptional Temperature Stability
- Low Power Loss and Lower Operating Temperature
- Higher Efficiency for Achieving Regulatory Compliance
- Low Thermal Resistance
- High Surge Capability
- Pb-Free and Halide-Free Packages are Available

Typical Applications

- Switching Power Supplies including Notebook / Netbook Adapters, ATX and Flat Panel Display
- High Frequency and DC-DC Converters
- Freewheeling and OR-ing diodes
- Reverse Battery Protection
- Instrumentation

Mechanical Characteristics

- Case: Epoxy, Molded
- Epoxy Meets Flammability Rating UL 94-0 @ 0.125 in
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Maximum for 10 sec

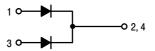


ON Semiconductor®

http://onsemi.com

VERY LOW FORWARD
VOLTAGE, LOW LEAKAGE
SCHOTTKY BARRIER
RECTIFIERS 30 AMPERES,
80 VOLTS

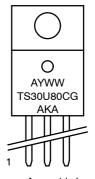
PIN CONNECTIONS





TO-220FB CASE 221AH

MARKING DIAGRAMS



A = Assembly Location

Y = Year WW = Work Week

AKA = Polarity Designator G = Pb-Free Package

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

MAXIMUM RATINGS

Rating		Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage		V _{RRM} V _{RWM} V _R	80	V
Average Rectified Forward Current (Rated V _R , T _C = 125°C)	Per device Per diode	I _{F(AV)}	30 15	А
Peak Repetitive Forward Current (Rated V _R , Square Wave, 20 kHz, T _C = 120°C)	Per device Per diode	I _{FRM}	60 30	А
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)		I _{FSM}	160	А
Operating Junction Temperature		TJ	-40 to +150	°C
Storage Temperature		T _{stg}	-40 to +150	°C
Voltage Rate of Change (Rated V _R)		dv/dt	10,000	V/μs

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

THERMAL CHARACTERISTICS

Rating		Symbol	Value	Unit
Maximum Thermal Resistance (insertion mounted to 1 oz FR4 Board)	Junction-to-Case	$R_{ heta JC}$	4.0	°C/W
(insertion mounted to 1 oz FR4 board)	Junction-to-Ambient	$R_{\theta JA}$	105	°C/W

^{1.} Junction-to-Case, using large Heatsink attached to device.

ELECTRICAL CHARACTERISTICS (Per Leg unless otherwise noted)

Rating	Symbol	Тур	Max	Unit
Maximum Instantaneous Forward Voltage (Note 3) $ \begin{aligned} & (I_F=5 \text{ A, } T_J=25^{\circ}\text{C}) \\ & (I_F=7.5 \text{ A, } T_J=25^{\circ}\text{C}) \\ & (I_F=15 \text{ A, } T_J=25^{\circ}\text{C}) \end{aligned} $ $ \begin{aligned} & (I_F=5 \text{ A, } T_J=125^{\circ}\text{C}) \\ & (I_F=7.5 \text{ A, } T_J=125^{\circ}\text{C}) \\ & (I_F=15 \text{ A, } T_J=125^{\circ}\text{C}) \end{aligned} $	V _F	0.47 0.52 0.66 0.42 0.48 0.60	- 0.80 - - 0.65	V
Maximum Instantaneous Reverse Current (Note 3) (Rated dc Voltage, T _J = 25°C) (Rated dc Voltage, T _J = 125°C)	I _R	15 10	200 35	μA mA

^{3.} Pulse Test: Pulse Width = 300 μ s, Duty Cycle $\leq 2.0\%$

ORDERING INFORMATION

Device	Package	Shipping
NTSJ30U80CTG	TO-220FP (Pb-Free)	50 Units / Rail

^{2.} Junction-to-Ambient, using with no Heatsink.

TYPICAL CHARACTERISITICS

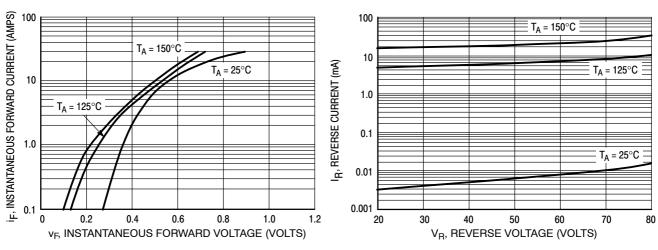


Figure 1. Typical Forward Voltage

Figure 2. Typical Reverse Current

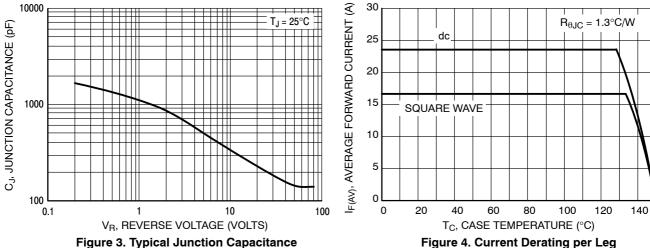


Figure 3. Typical Junction Capacitance

 $R_{\theta JC} = 1.3^{\circ}C/W$

60

55

50

45

40 35 30

25

20 15

10 5

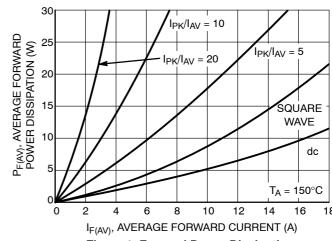
0

20

dc

SQUARE WAVE

I_{E(AV)}, AVERAGE FORWARD CURRENT (A)



T_C, CASE TEMPERATURE (°C) Figure 5. Current Derating, Case

100

Figure 6. Forward Power Dissipation

140

TYPICAL CHARACTERISITICS

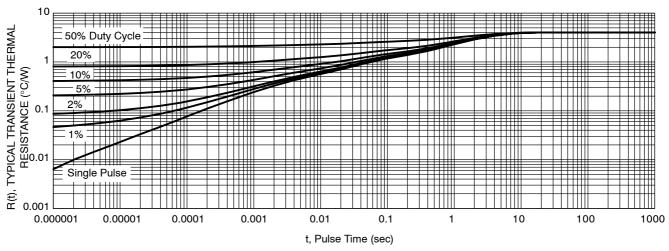
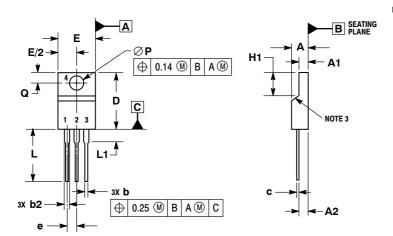


Figure 7. Typical Transient Thermal Response, Junction-to-Case

PACKAGE DIMENSIONS

TO-220 FULLPACK, 3-LEAD

CASE 221AH **ISSUE B**



- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.

- THE JUNE DIMENSION: MILLIMETERS.
 CONTROLLING DIMENSION: MILLIMETERS.
 CONTOUR UNCONTROLLED IN THIS AREA.
 DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH
 AND GATE PROTRUSIONS. MOLD FLASH AND GATE PROTRUSIONS NOT TO EXCEED 0.13 PER SIDE. THESE DIMENSIONS ARE TO BE MEASURED AT OUTERMOST EXTREME OF THE PLASTIC BODY.
- 5. DIMENSION b2 DOES NOT INCLUDE DAMBAR PROTRUSION. LEAD WIDTH INCLUDING PROTRUSION SHALL NOT EXCEED 2.00.

	MILLIMETERS		
DIM	MIN	MAX	
Α	4.30	4.70	
A1	2.50	2.90	
A2	2.50	2.70	
b	0.54	0.84	
b2	1.10	1.40	
С	0.49	0.79	
D	14.70	15.30	
Ε	9.70	10.30	
е	2.54 BSC		
H1	6.70	7.10	
Т	12.70	14.73	
L1		2.80	
Р	3.00	3.40	
Q	2.80	3.20	

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